



Standard Rectifier Module

 $V_{RRM} = 2x 1200 V$

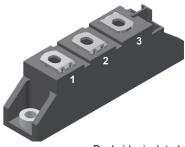
 $I_{\text{FAV}} = 50 \,\text{A}$

 $V_{\rm F} = 1.09 \, \rm V$

Phase leg

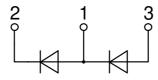
Part number

MDMA50P1200TG



Backside: isolated





Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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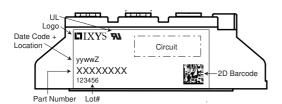


Rectifier				1	Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			1300	V	
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1200	٧	
I _R	reverse current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			50	μΑ	
		$V_R = 1200 \text{ V}$	$T_{VJ} = 150$ °C			1.5	mA	
V _F	forward voltage drop	I _F = 50 A	$T_{VJ} = 25^{\circ}C$			1.13	٧	
		$I_F = 100 A$				1.34	٧	
		$I_F = 50 \text{ A}$	T _{VJ} = 125°C			1.09	V	
		$I_F = 100 \text{ A}$				1.37	٧	
IFAV	average forward current	T _C = 100°C	T _{vJ} = 150°C			50	Α	
		rectangular $d = 0.5$						
V _{F0}	threshold voltage		T _{vJ} = 150°C			0.80	V	
r _F	slope resistance } for power	loss calculation only				5.7	mΩ	
R _{thJC}	thermal resistance junction to ca	ase				0.65	K/W	
R _{thCH}	thermal resistance case to heats	sink			0.2		K/W	
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			190	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			850	Α	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			920	Α	
		t = 10 ms; (50 Hz), sine	T _{vJ} = 150°C			725	Α	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			780	Α	
l 2t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			3.62	kA2s	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			3.52	kA2s	
		t = 10 ms; (50 Hz), sine	T _{vJ} = 150°C			2.63	kA2s	
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			2.53	kA2s	
C _J	junction capacitance	$V_R = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		27		pF	



MDMA50P1200TG

Package TO-240AA			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					200	Α
T _{VJ}	virtual junction temperatur	е			-40		150	°C
T _{op}	operation temperature			-40		125	°C	
T _{stg}	storage temperature			-40		125	°C	
Weight						76		g
M _D	mounting torque				2.5		4	Nm
$\mathbf{M}_{_{T}}$	terminal torque				2.5		4	Nm
d _{Spp/App}	oroonaga diatanaa an aurf	ace striking distance through air	terminal to terminal	13.0	9.7			mm
$d_{Spb/Apb}$	creepage distance on sum	ace Striking distance through an	terminal to backside	16.0	16.0			mm
V	isolation voltage t = 1 se		50/00 II 5140 I	•	4800			٧
		t = 1 minute	50/60 Hz, RMS; lisoL ≤ 1 mA		4000			٧



Part description

M = Module

D = Diode
M = Standard Rectifier

A = (up to 1800V) 50 = Current Rating [A]

P = Phase leg

1200 = Reverse Voltage [V]

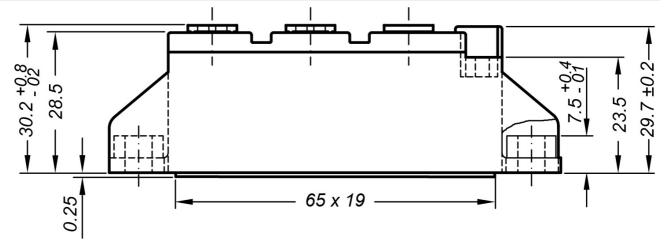
TG = TO-240AA

Orderin	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standar	MDMA50P1200TG	MDMA50P1200TG	Box	36	513029

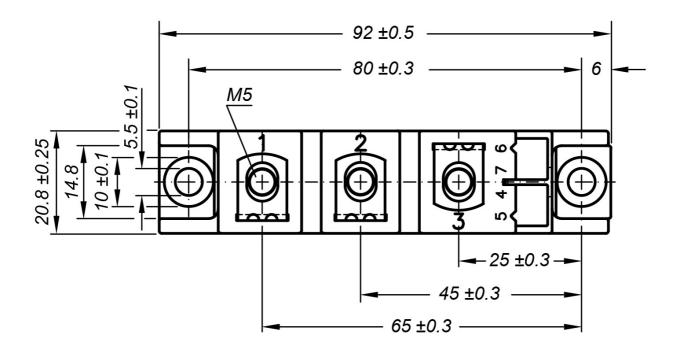
Equivalent Circuits for Simulation		* on die level	$T_{VJ} = 150^{\circ}C$	
$I \rightarrow V_0$)—[R_o]-	Rectifier		
V _{0 max}	threshold voltage	8.0		V
R_{0max}	slope resistance *	4.5		mΩ

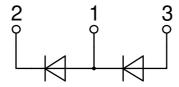


Outlines TO-240AA



General tolerance: DIN ISO 2768 class "c"









Rectifier

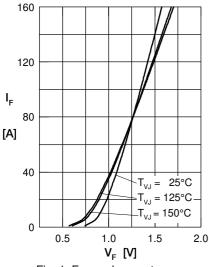


Fig. 1 Forward current versus voltage drop per diode

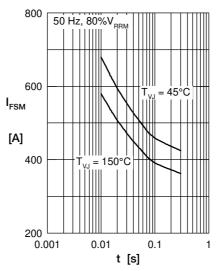


Fig. 2 Surge overload current vs. time per diode

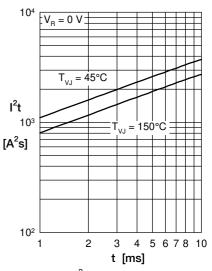


Fig. 3 I²t versus time per diode

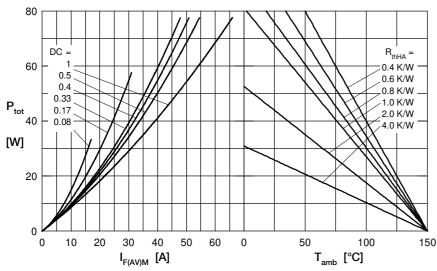


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

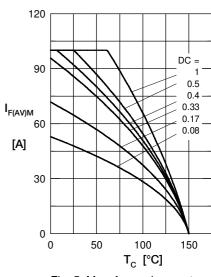


Fig. 5 Max. forward current vs. case temperature per diode

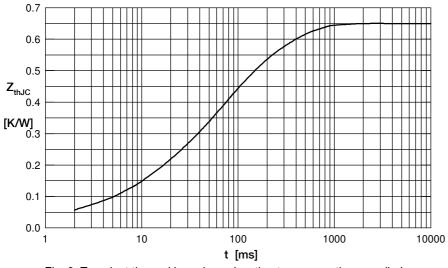


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t _i (s)
1	0.032	0.001
2	0.098	0.010
3	0.305	0.060
4	0.215	0.270

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T300N14TOF T3710N06TOF VT T390N16TOF T420N16TOF T460N24TOF T501N70TOH T560N16TOF T640N14TOF TD250N14KOF

TT600N16KOF TZ500N16KOF TZ240N36KOF TT210N12KOF NTE5710 TD180N16KOF TT240N28KOF TZ425N14KOF

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MDMA200P1600SA TT180N16KOF VS-ST333C08LFM0 VS-ST180C14C0L T1080N02TOF TD320N16SOF T360N22TOF

TZ810N22KOF